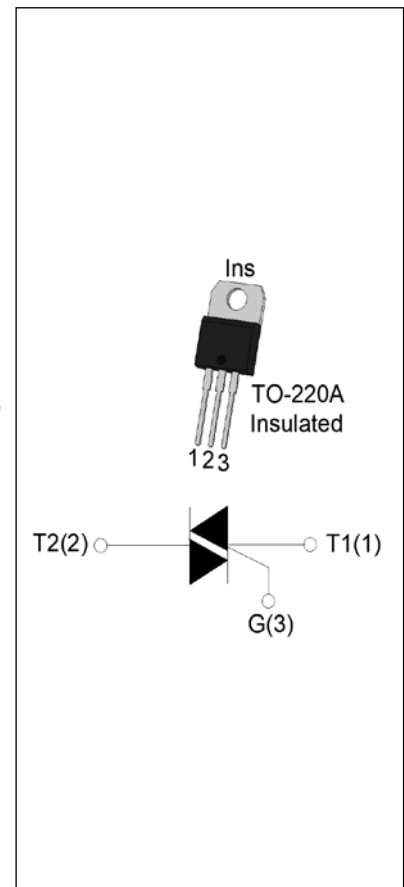


T1210H-8A 12A TRIAC

Rev.A.1.1

DESCRIPTION:

The T1210H-8A triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T1210H-8A provides a very high switching capability up to junction temperatures of 150°C. It can be driven directly through the MCU I/O port. By using an internal ceramic pad, T1210H-8A provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III}$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 114^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		132	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=150^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG. 7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^\circ C$ $R_L=3.3k\Omega$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	20	mA
		II		30	
I_H	$I_T=500mA$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150^\circ C$		MIN.	150	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150^\circ C$		MIN.	1.8	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$		TYP.	3	μs
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=17A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ C$	0.75	V
R_D	Dynamic resistance	$T_j=150^\circ C$	37	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=150^\circ C$	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.3	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ C/W$

ORDERING INFORMATION

<u>T</u>	<u>12</u>	<u>10</u>	<u>H</u>	<u>-8</u>	<u>A</u>
Triacs	$I_T(RMS):12A$				$A:TO-220A(Ins)$
	$10:I_{GT1-3} \leq 10mA$			$8:V_{DRM} / V_{RRM} \geq 800V$	
			High junction temperature		

MARKING

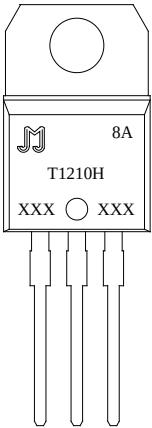
	<u>XXX</u> <u>XXX</u> Year _____ Production Code _____ Month _____
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FIG.1: Maximum power dissipation versus RMS on-state current

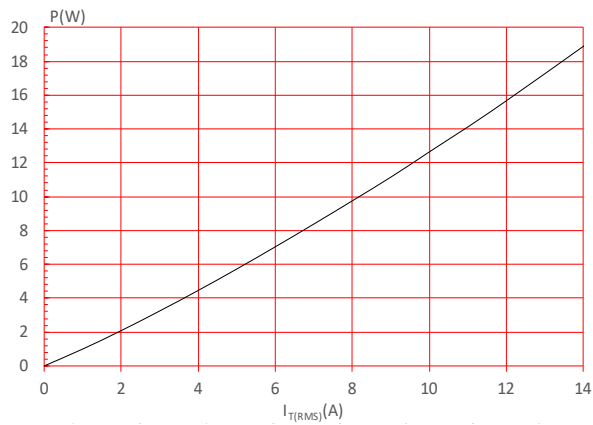


FIG.2: RMS on-state current versus case temperature

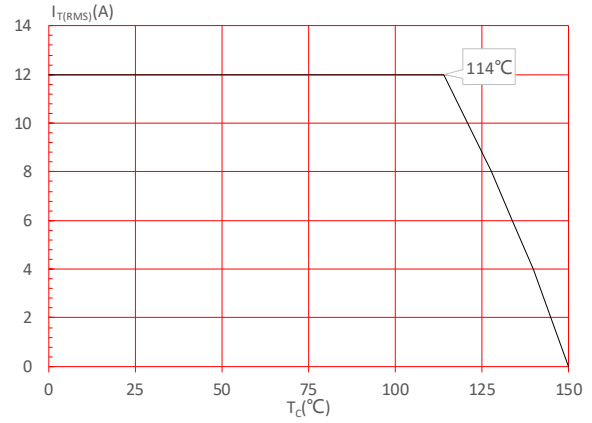


FIG.3: Surge peak on-state current versus number of cycles

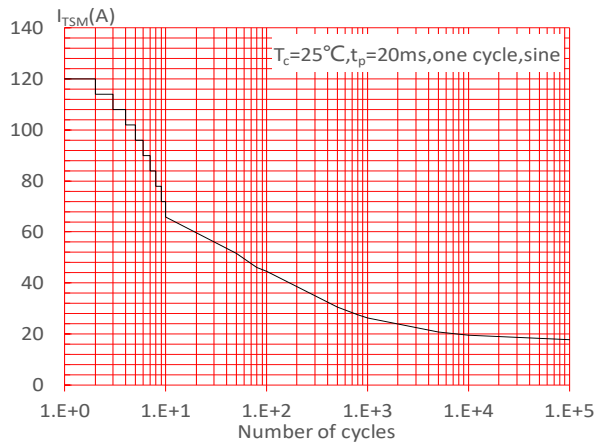


FIG.4: On-state characteristics

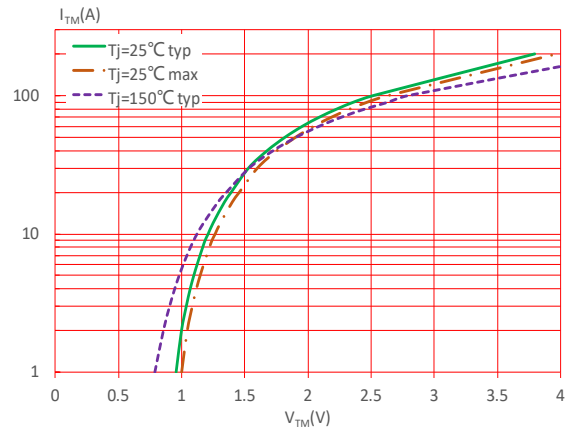


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

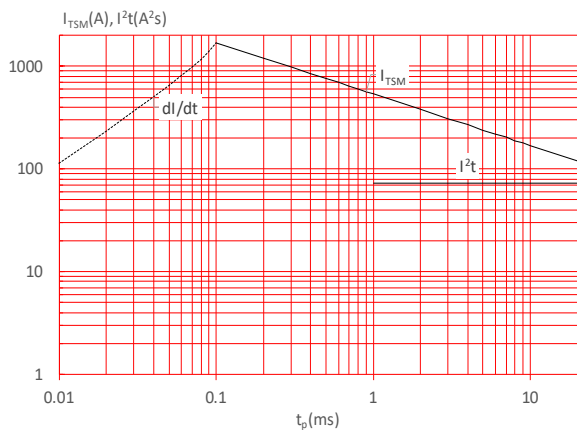


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

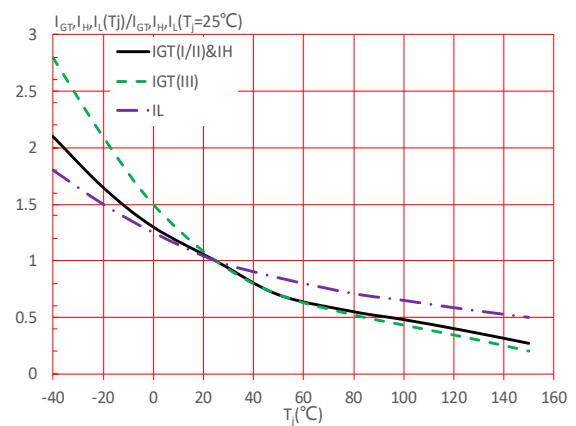
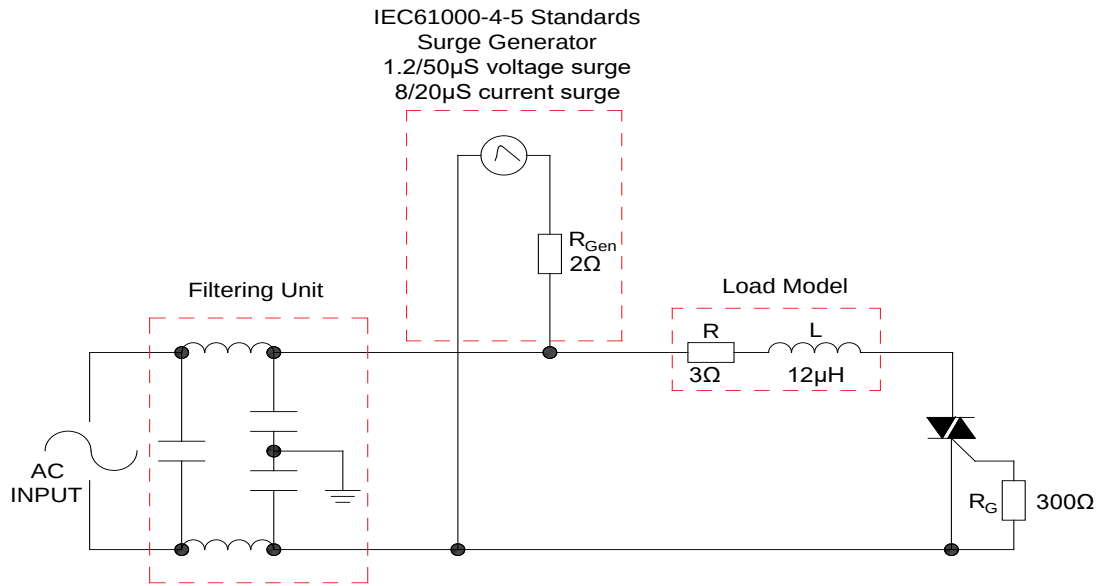


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

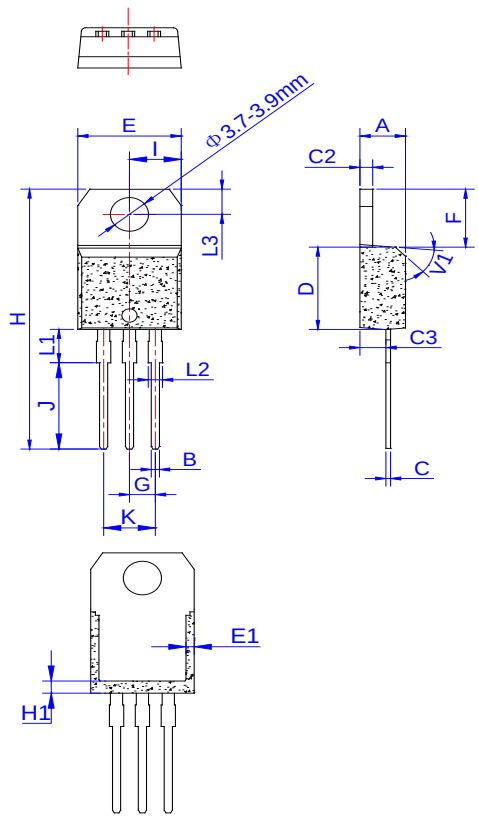
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
T1210H-8A	800	10	TO-220A(Ins)	50	Tube

Document Revision History

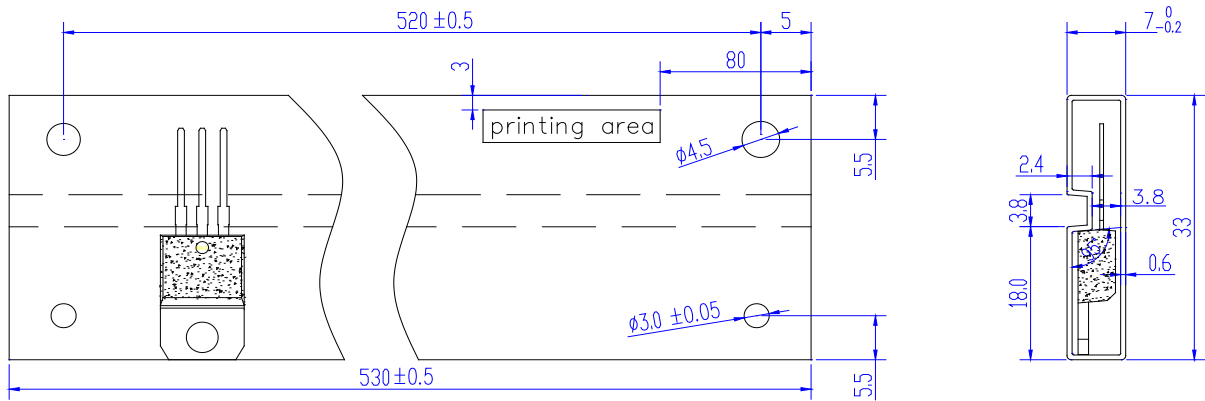
Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.40	0.386		0.409
E1	1.00		1.40	0.039		0.055
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.00		29.80	1.102		1.173
H1	1.80		2.20	0.071		0.087
I	4.80		5.20	0.189		0.205
J	9.55		9.95	0.376		0.392
K	4.80		5.20	0.189		0.205
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000

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